

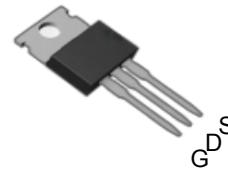
Features

- 100V/60A,
 $R_{DS(ON)} = 10\text{m}\Omega$ (typ.) @ $V_{GS}=10\text{V}$
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free and Green Devices Available
(RoHS Compliant)

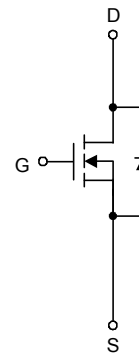
Applications

- Power Management for SMPS.
- DC-DC Converter.

Pin Description



Top View of TO-220



N-Channel MOSFET

Absolute Maximum Ratings (T_A = 25°C Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		100	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	
I _S	Diode Continuous Forward Current	T _C =25°C	60	A
I _D	Continuous Drain Current	T _C =25°C	60	A
		T _C =100°C	45	
I _{DM} ^a	Pulsed Drain Current	T _C =25°C	180	
P _D	Maximum Power Dissipation	T _C =25°C	104	W
		T _C =100°C	41	
R _{θJC}	Thermal Resistance-Junction to Case		1.2	°C/W
R _{θJA}	Thermal Resistance-Junction to Ambient		62.5	°C/W
I _{AS} ^b	Avalanche Current, Single pulse	L=0.5mH	25	A
E _{AS} ^b	Avalanche Energy, Single pulse	L=0.5mH	156	mJ

Note a : Pulse width limited by maximum junction temperature.

Note b : UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature T_J=25°C).

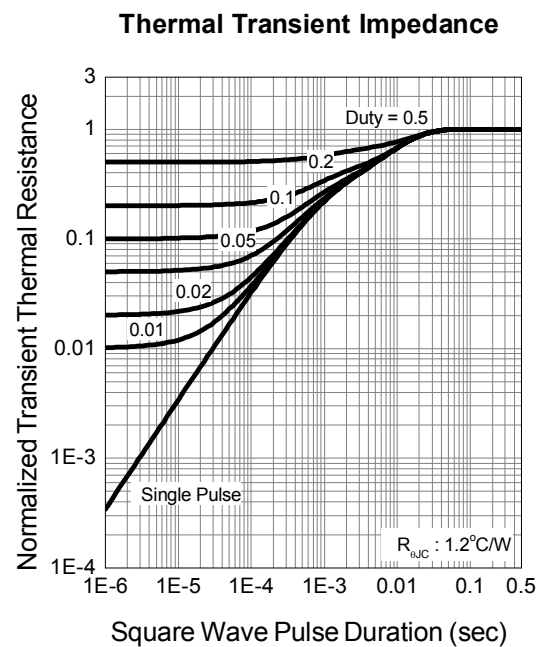
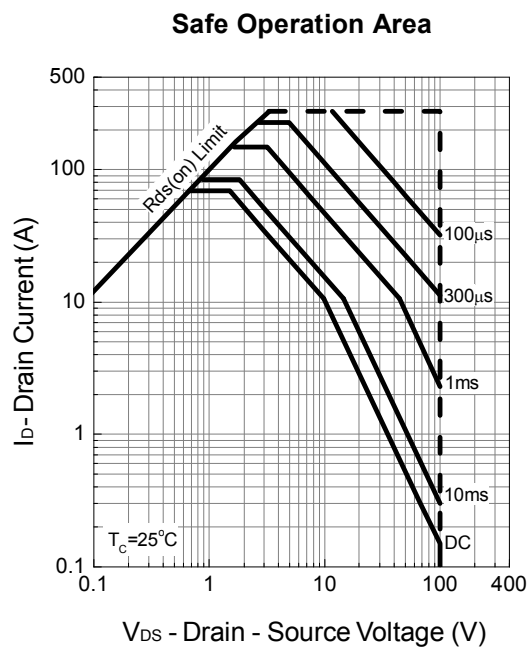
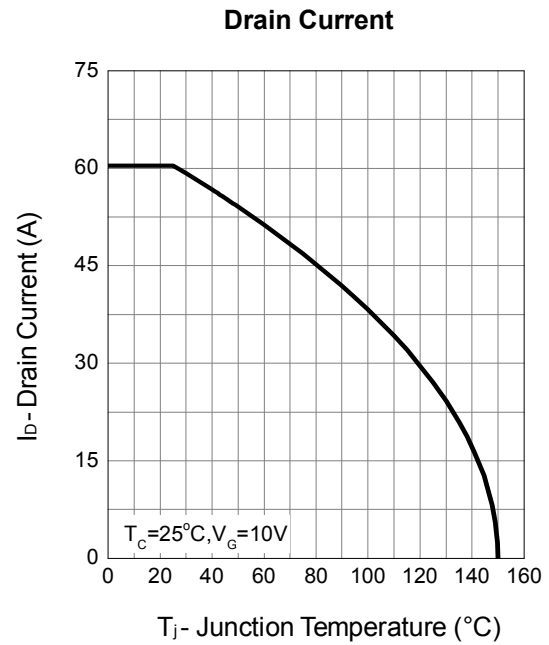
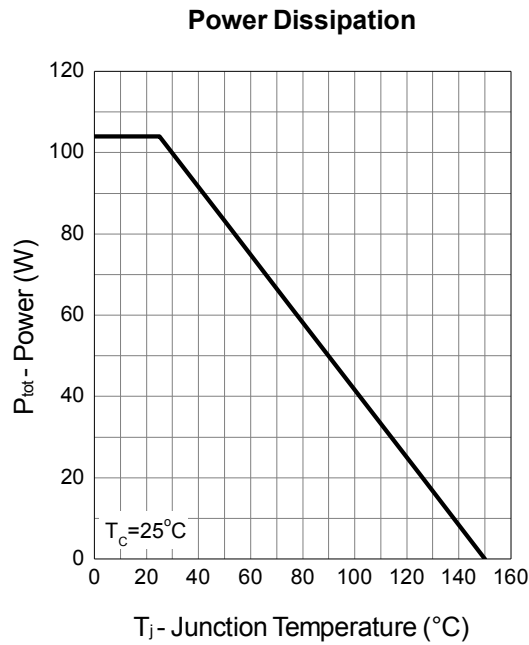
Electrical Characteristics (T_A = 25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	100	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =80V, V _{GS} =0V T _J =85°C	-	-	1 30	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	2.5	3	4	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^c	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =35A	-	10	14	mΩ
Diode Characteristics						
V _{SD} ^c	Diode Forward Voltage	I _{SD} =35A, V _{GS} =0V	-	0.9	1.3	V
t _{rr}	Reverse Recovery Time	I _{SD} =35A, dI _{SD} /dt=100A/μs	-	48	-	ns
Q _{rr}	Reverse Recovery Charge		-	80	-	nC
Dynamic Characteristics ^d						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	-	1.0	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =30V, Frequency=1.0MHz	-	3150	3500	pF
C _{oss}	Output Capacitance		-	413	-	
C _{rss}	Reverse Transfer Capacitance		-	70	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =30V, R _L =30Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	13	24	ns
t _r	Turn-on Rise Time		-	8	15	
t _{d(OFF)}	Turn-off Delay Time		-	30	54	
t _f	Turn-off Fall Time		-	65	117	
Gate Charge Characteristics ^d						
Q _g	Total Gate Charge	V _{DS} =50V, V _{GS} =10V, I _{DS} =35A	-	32	45	nC
Q _{gs}	Gate-Source Charge		-	10	-	
Q _{gd}	Gate-Drain Charge		-	8	-	

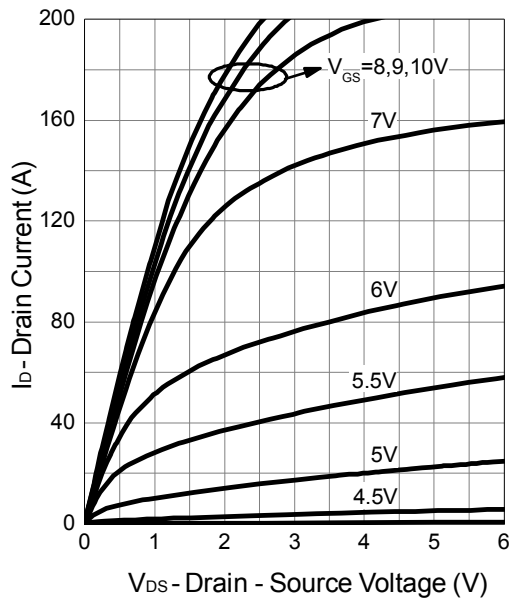
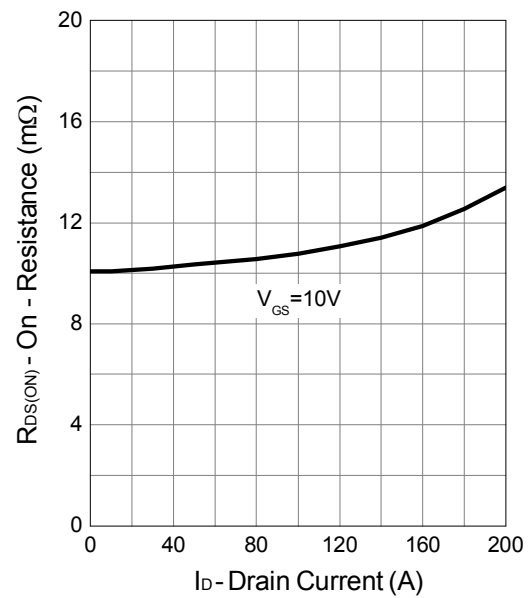
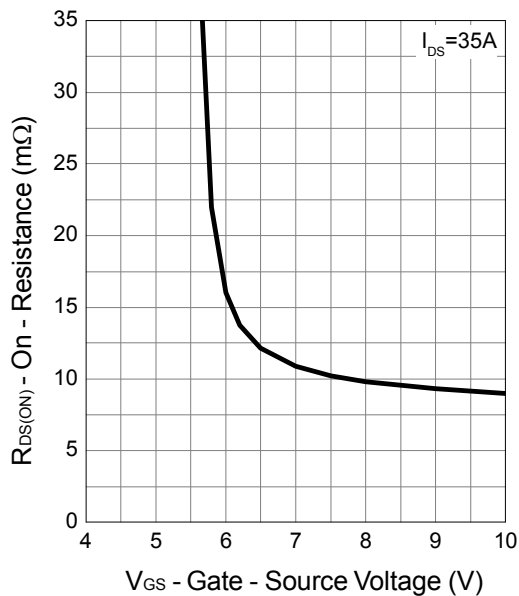
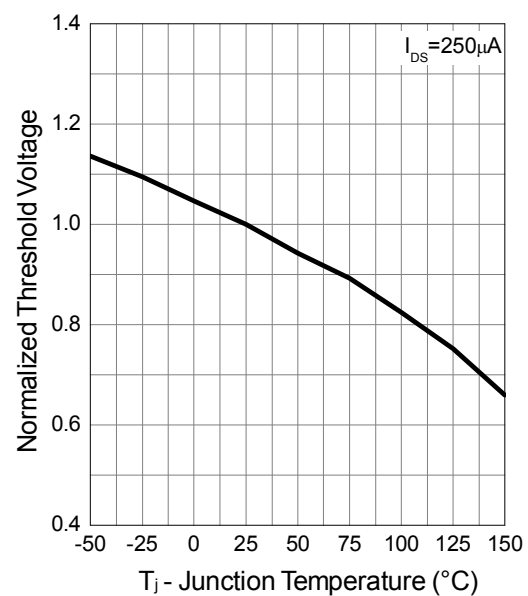
Note c : Pulse test ; pulse width≤300μs, duty cycle≤2%.

Note d : Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

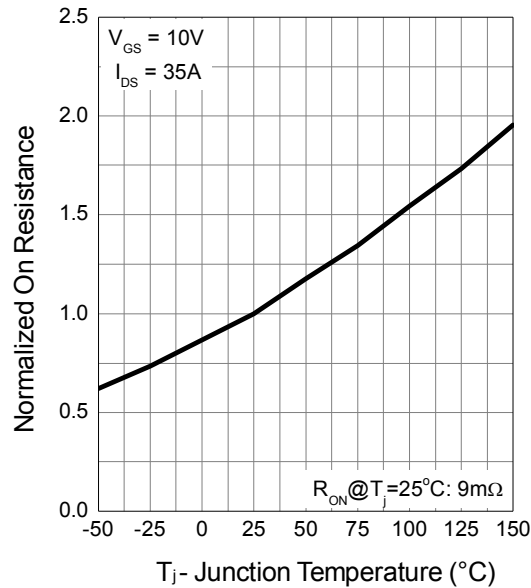


Typical Operating Characteristics (Cont.)

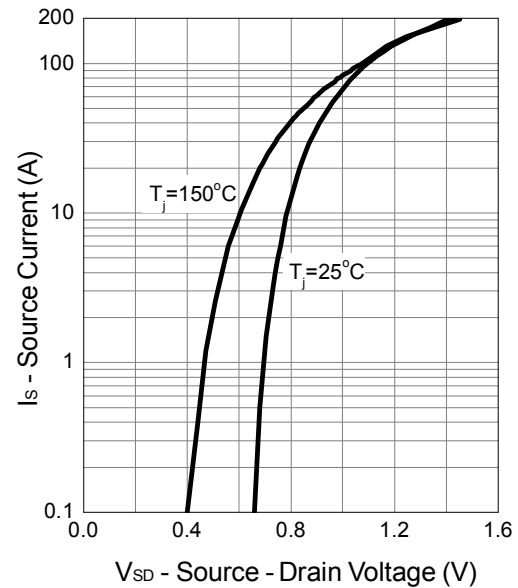
Output Characteristics

Drain-Source On Resistance

Gate-Source On Resistance

Gate Threshold Voltage


Typical Operating Characteristics (Cont.)

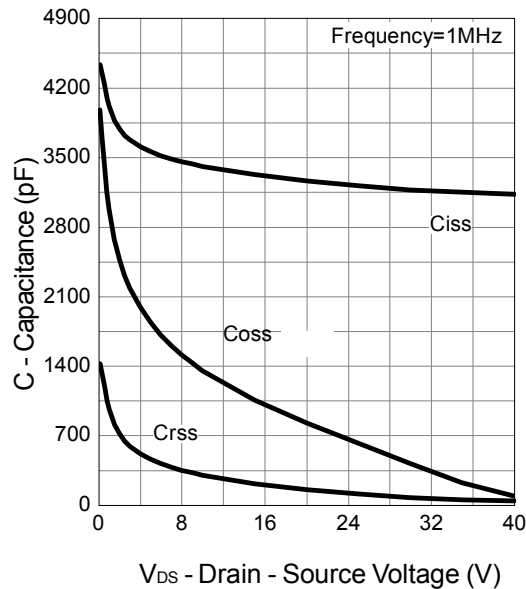
Drain-Source On Resistance



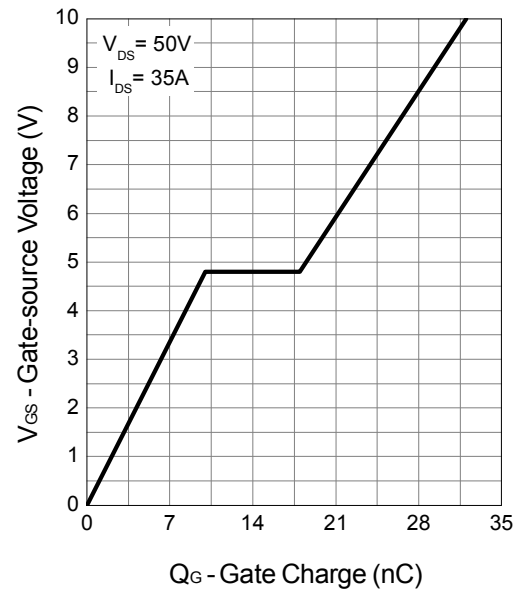
Source-Drain Diode Forward



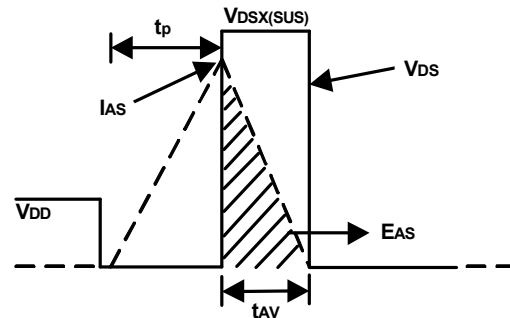
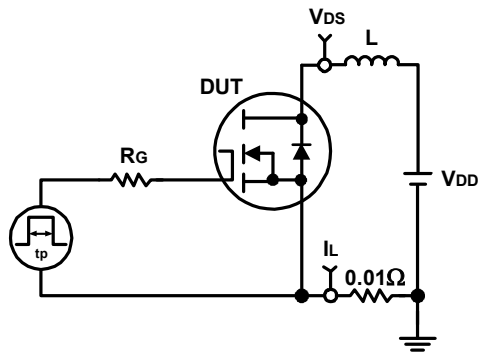
Capacitance



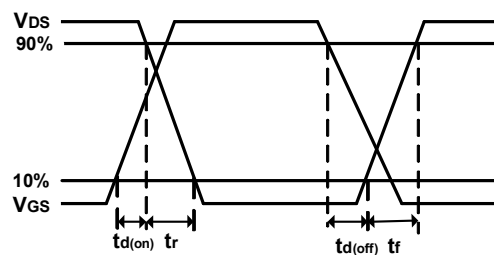
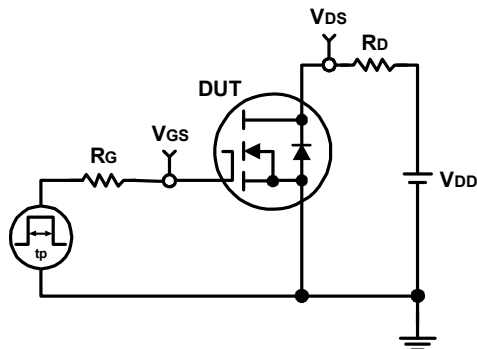
Gate Charge



Avalanche Test Circuit and Waveforms

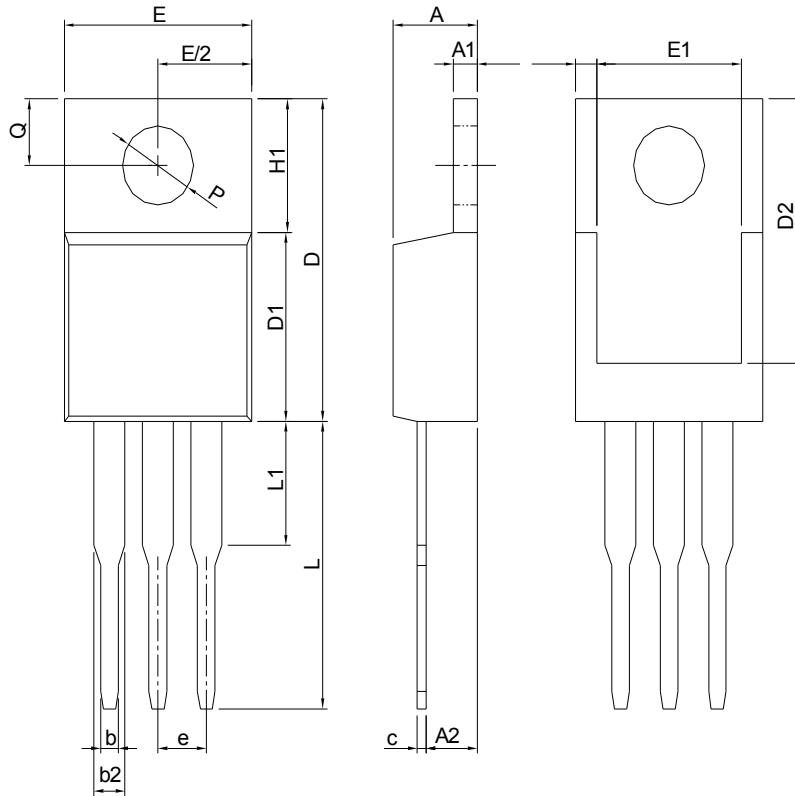


Switching Time Test Circuit and Waveforms



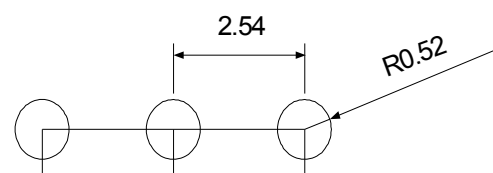
Package Information

TO-220



SYMBOL	TO-220			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	3.56	4.83	0.140	0.190
A1	0.51	1.40	0.020	0.055
A2	2.03	2.92	0.080	0.115
b	0.38	1.02	0.015	0.040
b2	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.22	16.51	0.560	0.650
D1	8.38	9.02	0.330	0.355
D2	12.19	13.65	0.480	0.537
E	9.65	10.67	0.380	0.420
E1	6.86	8.89	0.270	0.350
e	2.54 BSC		0.100 BSC	
H1	5.84	6.86	0.230	0.270
L	12.70	14.73	0.500	0.580
L1	-	6.35	-	0.250
P	3.53	4.09	0.139	0.161
Q	2.54	3.43	0.100	0.135

RECOMMENDED LAND PATTERN



UNIT: mm